

# ITC1000 1000 WATT, 50V, Pulsed Avionics 1030 MHz

## **GENERAL DESCRIPTION**

The ITC1000 is a common base bipolar transistor. It is designed for pulsed interrogator systems in the frequency band of 1030 MHz. The device has gold thin-film metallization for proven high MTTF. The transistor includes input returns for improved output rise time . Low thermal resistance package reduces junction temperature which extends the life time of the product.

# CASE OUTLINE 55SW, Style 1 Common Base

#### ABSOLUTE MAXIMUM RATINGS

## **Power Dissipation**

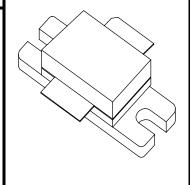
Device Dissipation<sup>1</sup> @25°C ( $P_d$ ) 3400 W Thermal Resistance<sup>1</sup> ( $\theta_{IC}$ ) .08°C/W

#### **Voltage and Current**

Collector-Base Voltage 65V Emitter-Base Voltage 3.5V Collector Current<sup>1</sup> 80A

#### **Temperatures**

Storage Temperature  $-40 \text{ to } +150^{\circ}\text{C}$ Operating Junction Temperature  $+200^{\circ}\text{C}$ 



# **ELECTRICAL CHARACTERISTICS @ 25°C**

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
BVebo <sup>2</sup>	Emitter-Base Breakdown(open)	Ie=50mA	3.5			V
BVces	Collector-Emitter Breakdown(shorted)	Ic=30mA	65			V
BVceo <sup>2</sup>	Collector-Emitter Breakdown (open)	Ic=30mA	30			V
h <sub>FE</sub> <sup>2</sup>	DC Current Gain	Ic=5A, Vce=5V	20	45	80	β

#### **FUNCTIONAL CHARACTERISTICS @ 25°C**

$G_{PB}$	Common Base Power Gain	$V_{cc} = 50V, F = 1030MHz, P_{out} = 1000W, \\ PW = 1\mu S, DF = 1\%$	8.0	8.5		dB
$\eta_{ m c}$	Collector Efficiency	$V_{cc} = 50V, F = 1030MHz, P_{out}=1000W, \\ PW=1\mu S, DF=1\%$	35	45		%
t <sub>r</sub>	Rise Time	$V_{cc} = 50V, F = 1030MHz, P_{out} = 1000W, \\ PW = 1\mu S, DF = 1\%$		50	80	nS
VSWR	Output Load Mismatch	$V_{cc} = 50V, F = 1030MHz, P_{out}=1000W, \\ PW=1\mu S, DF=1\%$			4:1	Ψ
$Z_{\rm in}$	Series Input Impedance (Circuit source impedance @ test cond.)	$V_{cc} = 50V, F = 1030MHz, P_{out} = 1000W, \\ PW = 1\mu S, DF = 1\%$	1.0-j2.0			Ω
$Z_{out}$	Series Output Impedance (Circuit load impedance @ test cond.)	$V_{cc} = 50V, F = 1030MHz, P_{out} = 1000W, \\ PW = 1\mu S, DF = 1\%$	0.6-j2.1			Ω

<sup>&</sup>lt;sup>1</sup> At rated output power and pulse conditions

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<sup>&</sup>lt;sup>2</sup> Contains input returns and cannot be measured Initial Issue May 1999

